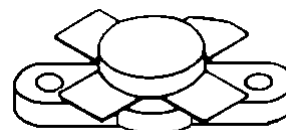


RF & MICROWAVE TRANSISTORS VHF MOBILE APPLICATIONS

- 160 MHz
- 13.6 VOLTS
- COMMON EMITTER
- $P_{OUT} = 30 \text{ W MIN. WITH } 10 \text{ dB GAIN}$

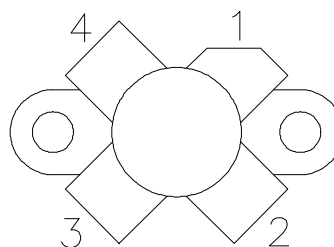


.380 4LFL (M113)
epoxy sealed

ORDER CODE
SD1274-01

BRANDING
SD1274-1

PIN CONNECTION



- | | |
|--------------|------------|
| 1. Collector | 3. Base |
| 2. Emitter | 4. Emitter |

DESCRIPTION

The SD1274-01 is a 13.6 V Class C epitaxial silicon NPN planar transistor designed primarily for VHF communications. The SD1274-01 utilizes an emitter ballasted die geometry to withstand severe load mismatch conditions.

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	36	V
V_{CEO}	Collector-Emitter Voltage	16	V
V_{CES}	Collector-Emitter Voltage	36	V
V_{EBO}	Emitter-Base Voltage	4.0	V
I_C	Device Current	8.0	A
P_{DISS}	Power Dissipation	70	W
T_J	Junction Temperature	+200	$^{\circ}\text{C}$
T_{STG}	Storage Temperature	- 65 to +150	$^{\circ}\text{C}$

THERMAL DATA

$R_{TH(j-c)}$	Junction-Case Thermal Resistance	1.2	$^{\circ}\text{C/W}$
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ELECTRICAL SPECIFICATIONS ($T_{case} = 25^{\circ}C$)

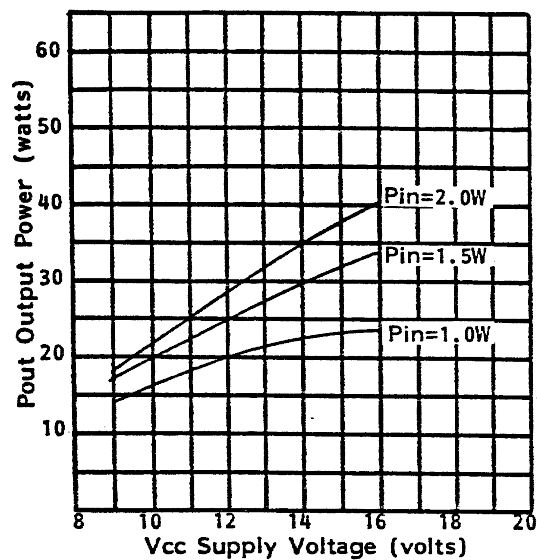
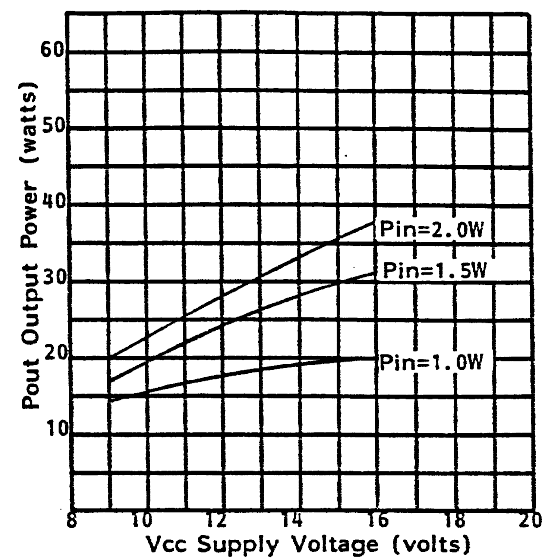
STATIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV_{CES}	$I_C = 15mA$	$V_{BE} = 0mA$	36	—	—	V
BV_{CEO}	$I_C = 50mA$	$I_B = 0mA$	16	—	—	V
BV_{EBO}	$I_E = 5mA$	$I_C = 0mA$	4.0	—	—	V
I_{CBO}	$V_{CB} = 15V$	$I_E = 0mA$	—	—	5	mA
h_{FE}	$V_{CE} = 5V$	$I_C = 250mA$	20	—	—	—

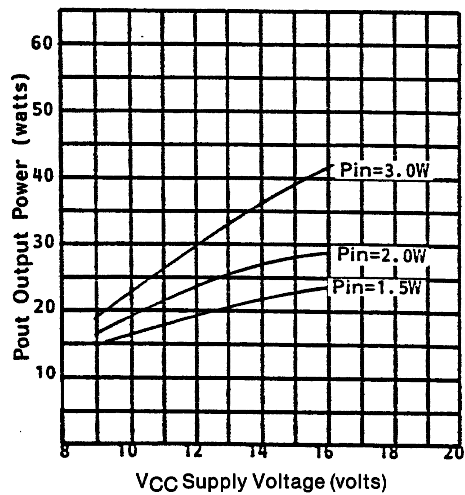
DYNAMIC

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P_{OUT}	$f = 160\text{ MHz}$	$P_{IN} = 3.0\text{ W}$	$V_{CE} = 13.6\text{ V}$	30	—	—	W
G_P	$f = 160\text{ MHz}$	$P_{IN} = 3.0\text{ W}$	$V_{CE} = 13.6\text{ V}$	10	—	—	dB
C_{OB}	$f = 1\text{ MHz}$	$V_{CB} = 15\text{ V}$		—	95	—	pF

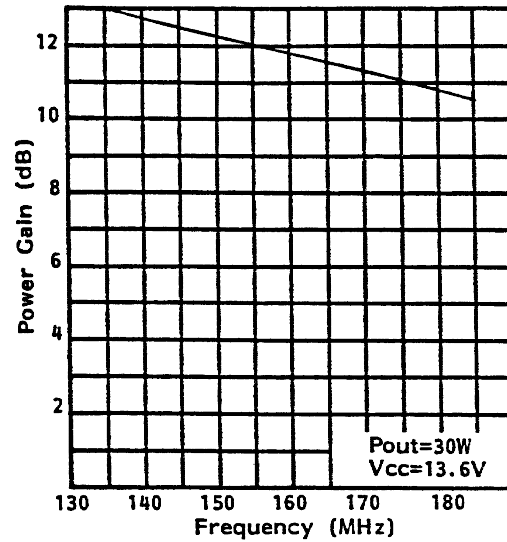
TYPICAL PERFORMANCE

POWER OUTPUT vs SUPPLY VOLTAGE
(136 MHz)POWER OUTPUT vs SUPPLY VOLTAGE
(150 MHz)

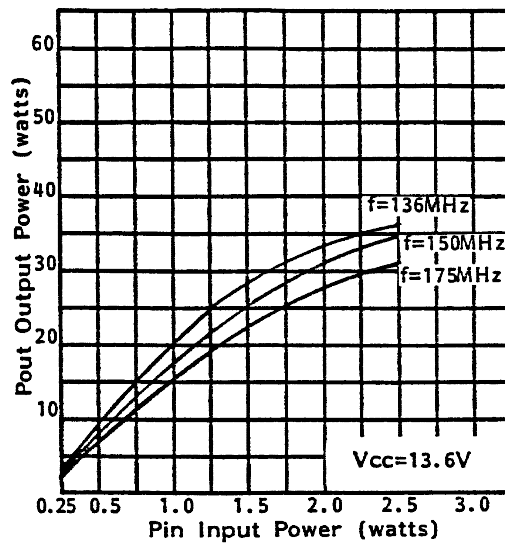
TYPICAL PERFORMANCE (cont'd)

POWER OUTPUT vs SUPPLY VOLTAGE
(175 MHz)

POWER GAIN vs FREQUENCY



POWER OUTPUT vs POWER INPUT



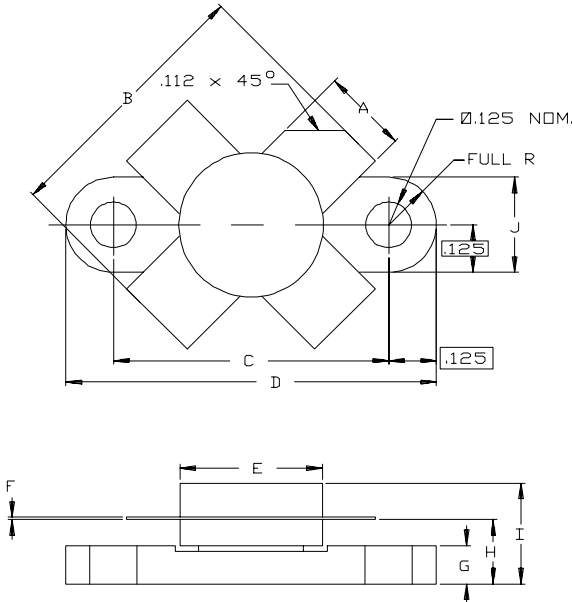
IMPEDANCE DATA

FREQ.	Z_{IN} (Ω)	Z_{CL} (Ω)
175 MHz	$1.0 + j 0.4$	$2.3 + j 0.1$

$P_{IN} = 3.0 W$
 $V_{CE} = 12.5 V$

PACKAGE MECHANICAL DATA

Ref.: Dwg. No.12-0113



SGS-THOMSON MICROELECTRONICS		
	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.220/5,59	.230/5,84
B	.785/19,94	
C	.720/18,29	.730/18,54
D	.970/24,64	.980/24,89
E		.385/9,78
F	.004/0,10	.006/0,15
G	.085/2,16	.105/2,67
H	.160/4,06	.180/4,57
I		.280/7,11
J	.240/6,10	.255/6,48

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